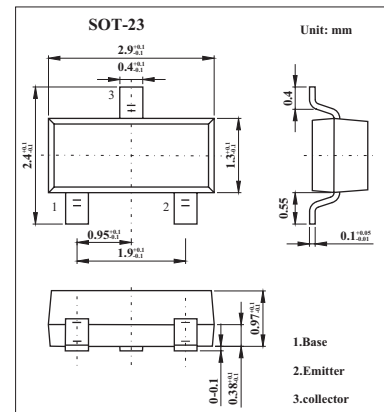


## Silicon PNP Epitaxial

## 2SA1617

## ■ Features

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-55	V
Collector-emitter voltage	$V_{CE0}$	-50	V
Emitter-base voltage	$V_{EB0}$	-5	V
Collector current	$I_c$	-100	mA
Collector dissipation	$P_c$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_c = -10\mu\text{A}$ , $I_E = 0$	-55			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_c = -1\text{mA}$ , $R_{BE} = \infty$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E = -10\mu\text{A}$ , $I_c = 0$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -30\text{V}$ , $I_E = 0$			-0.5	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -2\text{V}$ , $I_c = 0$			-0.5	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = -12\text{V}$ , $I_c = -2\text{mA}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -10\text{mA}$ , $I_B = -1\text{mA}$			-0.2	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = -12\text{V}$ , $I_c = -2\text{mA}$			-0.8	V

■  $h_{FE}$  Classification

Marking	VI	
Rank	B	C
$h_{FE}$	100~200	160~320